

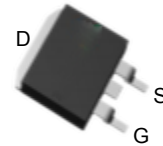
Features

- 68V/80A,
 $R_{DS(ON)} = 7.5\text{m}\Omega$ (typ.) @ $V_{GS} = 10\text{V}$
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)

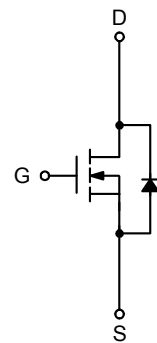
Applications

- Synchronous Rectification.
- Power Management in Inverter Systems.

Pin Description



Top View of TO-263



N-Channel MOSFET

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _A =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		68	V
V _{GSS}	Gate-Source Voltage		±25	
T _J	Maximum Junction Temperature		155	°C
T _{STG}	Storage Temperature Range		-55 to 155	
I _S	Diode Continuous Forward Current	T _C =25°C	80	A
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	240	A
I _D	Continuous Drain Current	T _C =25°C	80	A
		T _C =100°C	60	
P _D	Maximum Power Dissipation	T _C =25°C	83	W
		T _C =100°C	41	
R _{θJC}	Thermal Resistance-Junction to Case		1.8	°C/W
R _{θJA}	Thermal Resistance-Junction to Ambient		62.5	
E _{AS}	Avalanche Energy, Single Pulsed	L=1mH	200	mJ

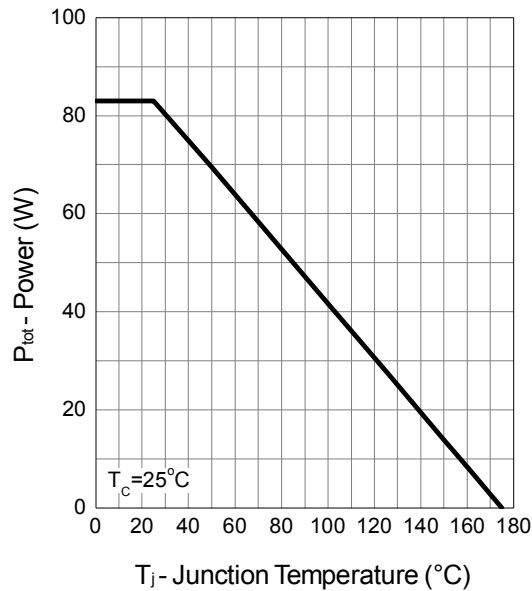
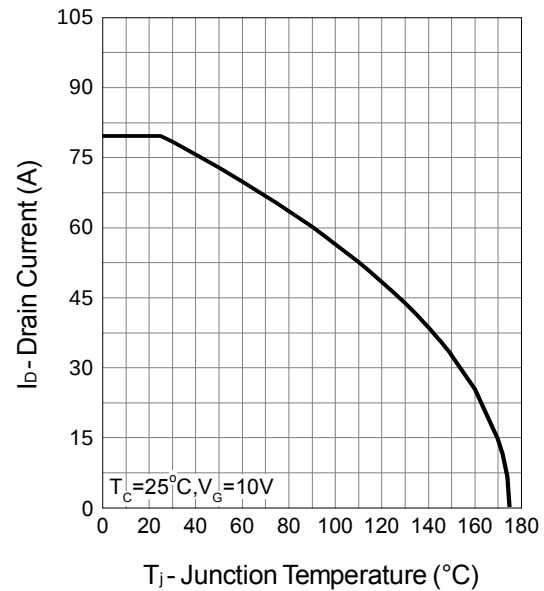
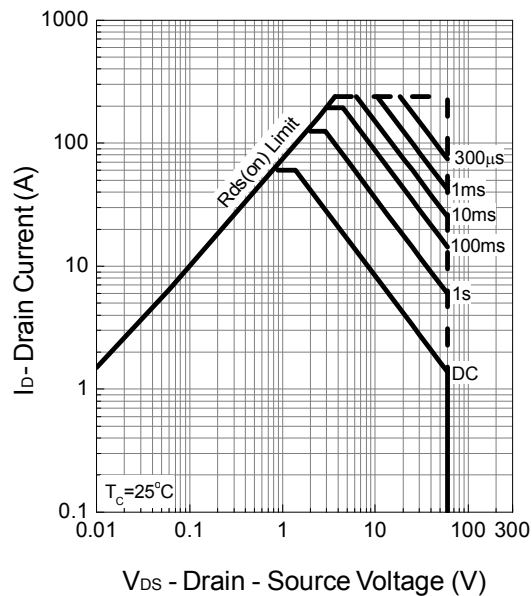
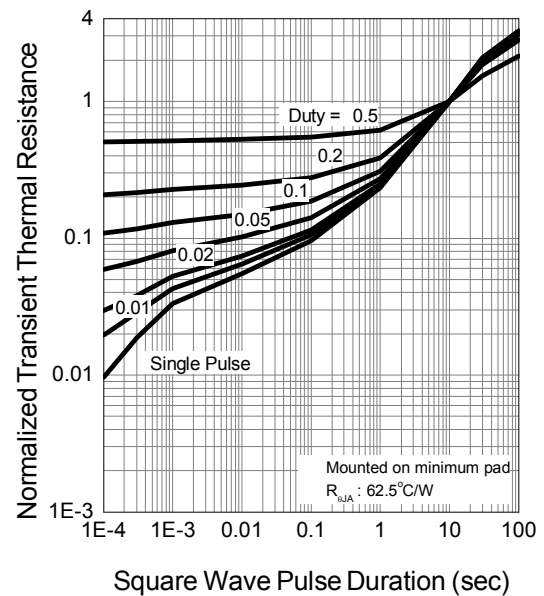
Electrical Characteristics (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions				Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	68	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =55V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =30A	-	7.5	9	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =30A, V _{GS} =0V	-	0.85	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =30A, di _{SD} /dt=100A/μs	-	45	-	ns
Q _{rr}	Reverse Recovery Charge		-	60	-	nC
Dynamic Characteristics ^b						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	2	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	2400	-	pF
C _{oss}	Output Capacitance		-	245	-	
C _{rss}	Reverse Transfer Capacitance		-	140	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	20	30	ns
t _r	Turn-on Rise Time		-	18	33	
t _{d(OFF)}	Turn-off Delay Time		-	50	90	
t _f	Turn-off Fall Time		-	25	45	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =30A	-	45	63	nC
Q _{gs}	Gate-Source Charge		-	15	-	
Q _{gd}	Gate-Drain Charge		-	15	-	

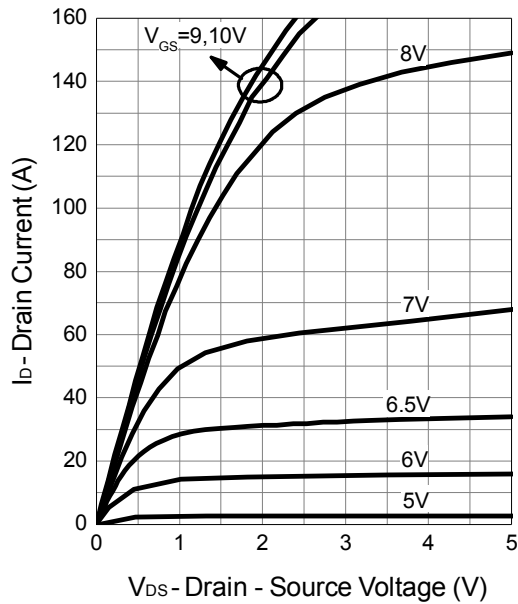
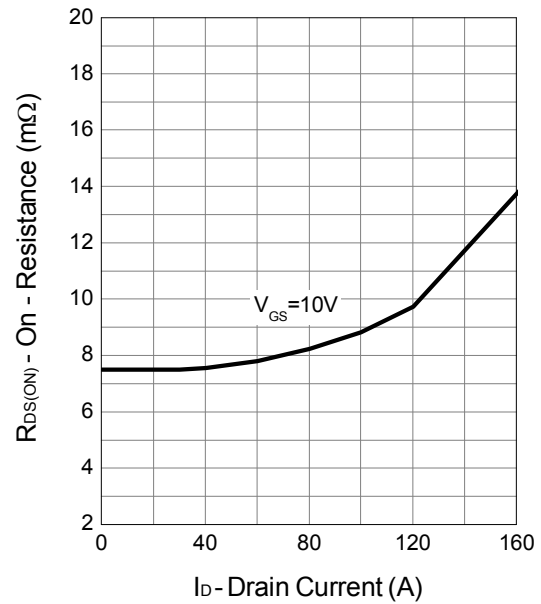
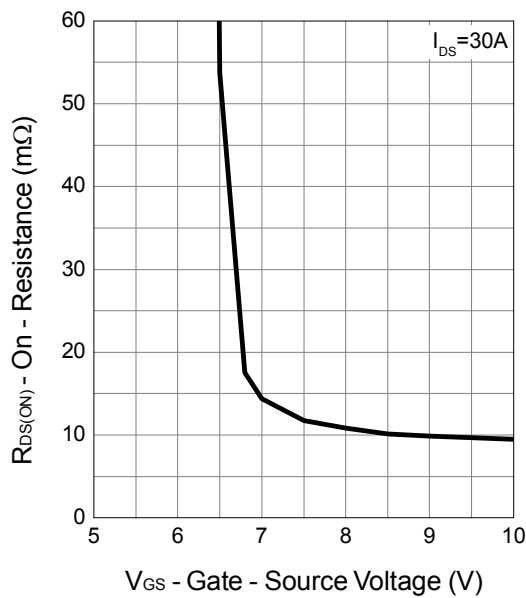
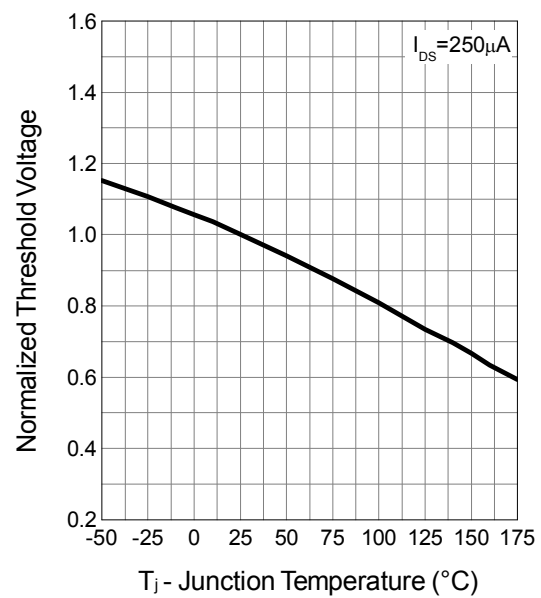
Note a : Pulse test ; pulse width≤300μs, duty cycle≤2%.

Note b : Guaranteed by design, not subject to production testing.

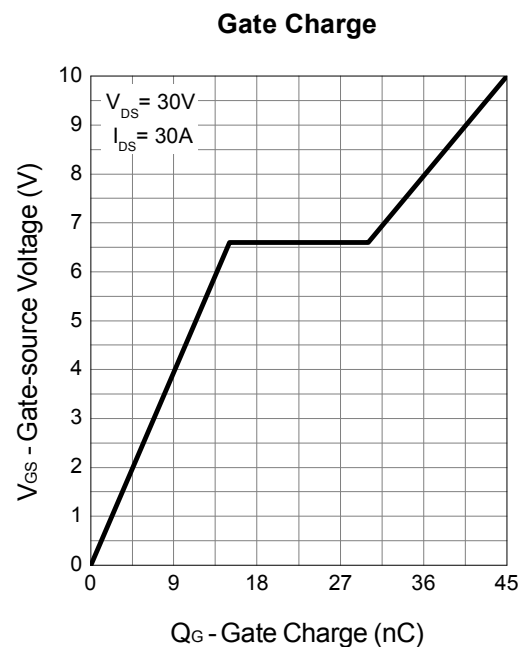
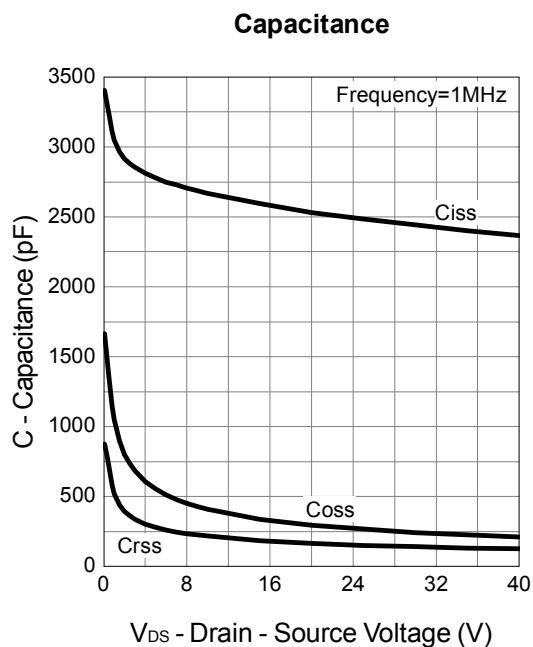
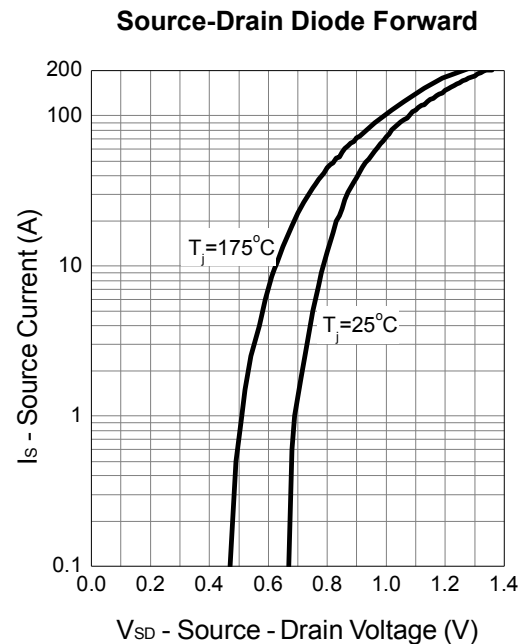
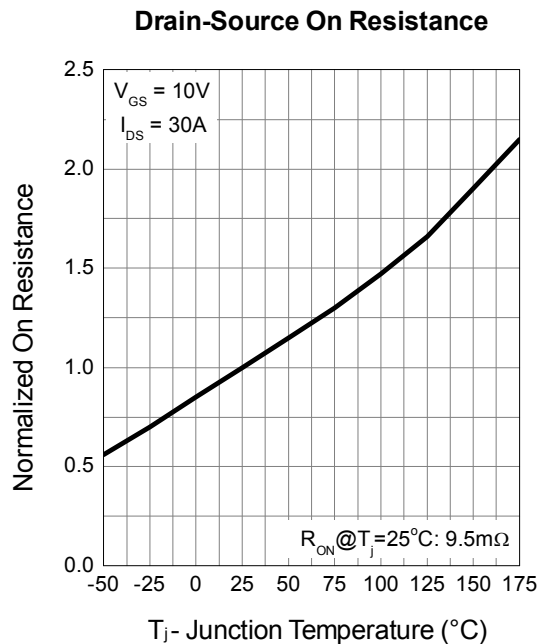
Typical Operating Characteristics

Power Dissipation

Drain Current

Safe Operation Area

Thermal Transient Impedance


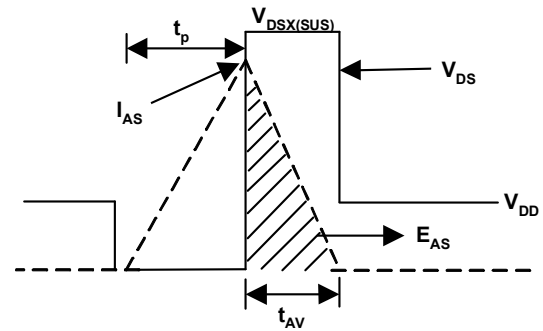
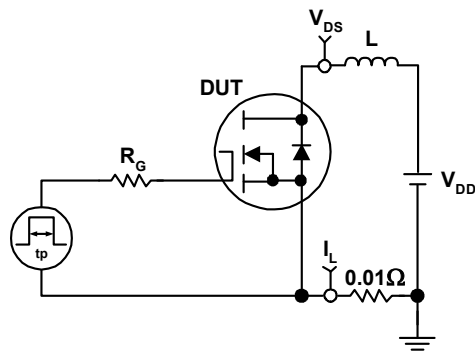
Typical Operating Characteristics (Cont.)

Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


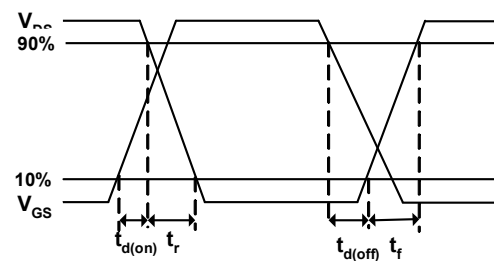
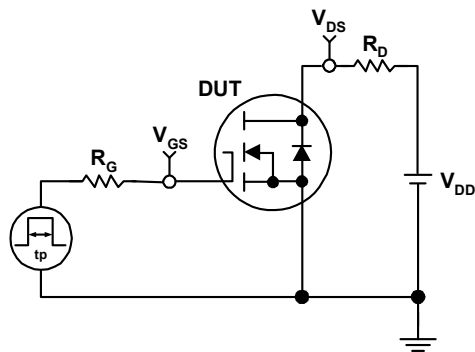
Typical Operating Characteristics (Cont.)



Avalanche Test Circuit and Waveforms

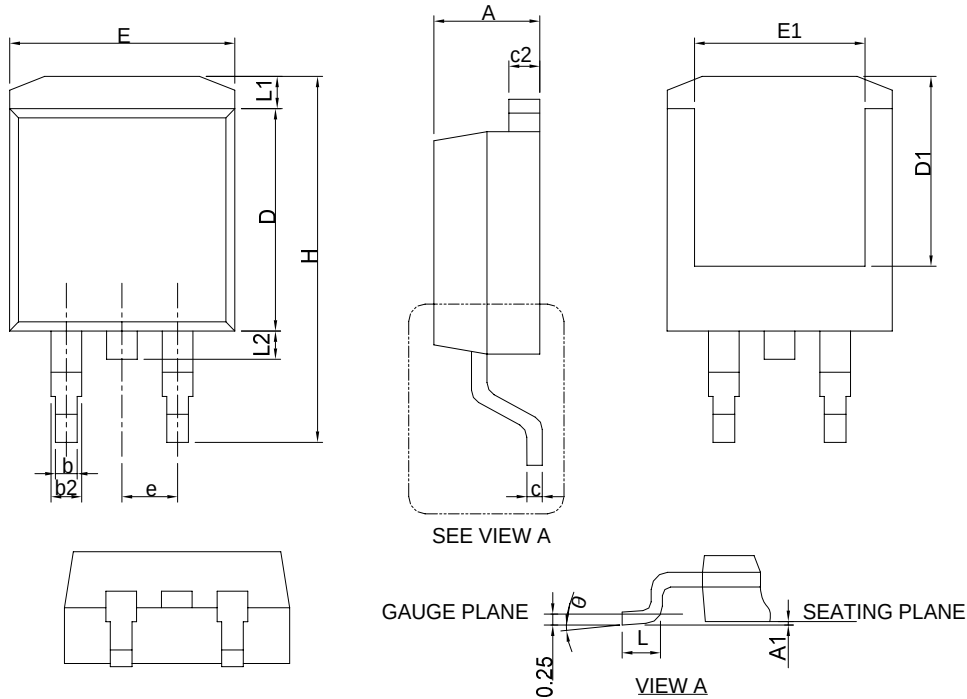


Switching Time Test Circuit and Waveforms



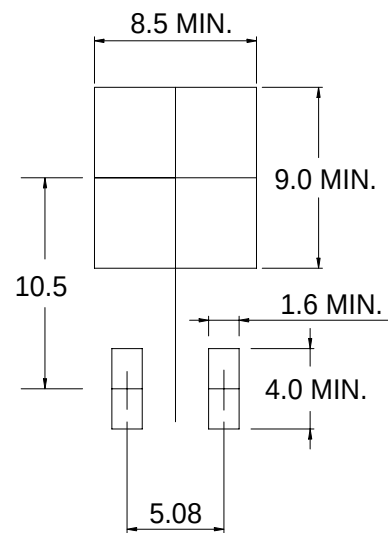
Package Information

TO-263



SYMBOL	TO-263			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b2	1.14	1.78	0.045	0.070
c	0.38	0.74	0.015	0.029
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380
D1	6.00	9.00	0.236	0.354
E	9.65	11.43	0.380	0.450
E1	6.22	9.00	0.245	0.354
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.68	-	0.066
L2	-	1.78	-	0.070
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



UNIT: mm

Note : Follow JEDEC TO-263 AB.